

Automotive AEC-Q100 Qualified Low Skew, 1-To-2 LVCMOS / LVTTTL Fanout Buffer

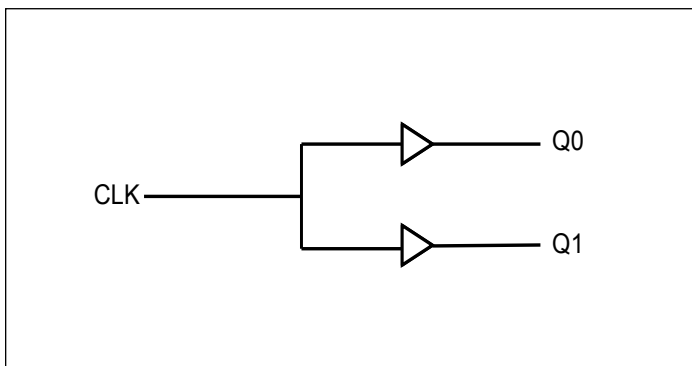
Features

- 2 LVCMOS / LVTTTL outputs
- LVCMOS / LVTTTL clock input accepts LVCMOS or LVTTTL input levels
- Maximum output frequency: 250MHz
- Output skew: 25ps (typical)
- Part-to-part skew: 250ps (typical)
- Small 8 lead SOIC package saves board space
- Full 3.3V, 2.5V operation modes
- AEC-Q100 Qualified
- Automotive Grade 2 temperature range (-40 to 105 °C)
- Automotive Grade 3 temperature range (-40 to 85 °C)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free “Green” Device (Note 3)
- The PI6C49CB02Q is suitable for automotive applications requiring specific change control and is AEC-Q100 qualified, has a grade 2, -40 to 105 °C temperature rating and grade 3, -40 to 85 °C temperature rating, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.
- Package: 8-Pin, SOIC (W)

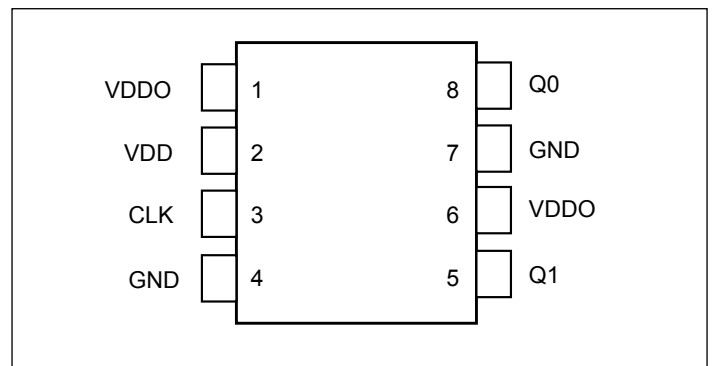
Description

The PI6C49CB02Q is an automotive qualified low skew, 1-to-2 LVCMOS/LVTTTL High Performance Fanout Buffer. The PI6C49CB02Q has a single ended clock input. The single ended clock input accepts LVCMOS or LVTTTL input levels. The PI6C49CB02Q features a pair of LVCMOS/LVTTTL outputs. Guaranteed output and part-to-part skew characteristics make the PI6C49CB02Q ideal for clock distribution applications demanding well defined performance and repeatability.

Block Diagram



Pin Assignment



Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Descriptions

| Pin# | Pin Name | Pin Type | | Pin Description |
|------|----------|----------|-----------|---|
| 1, 6 | VDDO | Power | | Output supply pins. |
| 2 | VDD | Power | | Core supply pin. |
| 3 | CLK | Input | Pull-down | LVC MOS / LV TTL clock input. |
| 4, 7 | GND | Power | | Power supply ground. |
| 5 | Q1 | Output | | Single clock output. LVC MOS / LV TTL interface levels. |
| 8 | Q0 | Output | | Single clock output. LVC MOS / LV TTL interface levels. |

Note: *Pull-down* refer to internal input resistors, typical values in Pin Characteristics table.

Pin Characteristics

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|----------------|--------------------------|-----------------|------|------|------|------------|
| C_N | Capacitance | | | 4 | | pF |
| $R_{PULLDOWN}$ | Input Pull-down Resistor | | | 51 | | k Ω |
| R_{OUT} | Output Impedance | | 5 | 7 | 12 | Ω |

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

| | |
|---|--------------------|
| Maximum Supply Voltage, VDD, VDDO | 4.6V |
| Inputs, V_I | -0.5V to VDD+0.5V |
| Output, V_O | -0.5V to VDDO+0.5V |
| Storage Temperature | -65°C to 150°C |
| ESD Protection (HBM) | 2000V |
| Junction Temperature | 125°C (Max) |

Note:

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the DC Characteristics or AC Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Recommended Operation Conditions

| Parameter | Min. | Typ. | Max. | Units |
|--|--------|------|--------|-------|
| Ambient Operating Temperature (Automotive Grade 2) | -40 | | +105 | °C |
| Ambient Operating Temperature (Automotive Grade 3) | -40 | | +85 | °C |
| Power Supply Voltage (measured in respect to GND) | +2.375 | | +3.465 | V |

Power Supply DC Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|--------|-----------------------------|---|-------|------|-------|-------|
| VDD | Core Supply Voltage | 3.3V Operation | 3.135 | 3.3 | 3.465 | V |
| | | 2.5V Operation | 2.375 | 2.5 | 2.625 | |
| VDDO | Output Power Supply Voltage | 3.3V Supply | 3.135 | 3.3 | 3.465 | V |
| | | 2.5V Supply | 2.375 | 2.5 | 2.625 | |
| IDD | Power Supply Current | $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ | | | 5 | mA |
| IDDO | Output Supply Current | Unloaded, 25 MHz, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ | | | 6.5 | mA |
| IDD | Power Supply Current | $T_A = -40^\circ\text{C to } 105^\circ\text{C}$ | | | 5 | mA |
| IDDO | Output Supply Current | Unloaded, 25 MHz, $T_A = -40^\circ\text{C to } 105^\circ\text{C}$ | | | 6.5 | mA |

Note: Parameters measured up to f_{max} unless otherwise noted.

LVCMOS / LVTTTL DC Characteristics, $T_A = -40^{\circ}\text{C}$ to 85°C

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|----------|---------------------|--|------|------|---------|---------------|
| V_{IH} | Input High Voltage | VDD = 3.3V | 2 | | VDD+0.3 | V |
| | | VDD = 2.5V | 1.7 | | VDD+0.3 | |
| V_{IL} | Input Low Voltage | VDD = 3.3V | -0.3 | | 0.8 | V |
| | | VDD = 2.5V | -0.3 | | 0.8 | |
| I_{IH} | Input High Current | VDD = $V_{IN} = 3.465\text{V}$ | | | 100 | μA |
| | | VDD = $V_{IN} = 2.625\text{V}$ | | | 80 | |
| I_{IL} | Input Low Current | VDD = 3.465V, $V_{IN} = 0\text{V}$ | -5 | | | μA |
| | | VDD = 2.625V, $V_{IN} = 0\text{V}$ | -5 | | | |
| V_{OH} | Output High Voltage | VDDO = 3.3V $I_{OH} = -100\mu\text{A}$ | 2.9 | | | V |
| | | VDDO = 2.5V $I_{OH} = -100\mu\text{A}$ | 2.2 | | | V |
| V_{OL} | Output Low Voltage | VDDO = 3.3V $I_{OL} = 100\mu\text{A}$ | | | 0.2 | V |
| | | VDDO = 2.5V $I_{OL} = 100\mu\text{A}$ | | | 0.2 | V |

LVCMOS / LVTTTL DC Characteristics, $T_A = -40^{\circ}\text{C}$ to 105°C

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|----------|---------------------|--|------|------|---------|---------------|
| V_{IH} | Input High Voltage | VDD = 3.3V | 2 | | VDD+0.3 | V |
| | | VDD = 2.5V | 1.7 | | VDD+0.3 | |
| V_{IL} | Input Low Voltage | VDD = 3.3V | -0.3 | | 0.8 | V |
| | | VDD = 2.5V | -0.3 | | 0.8 | |
| I_{IH} | Input High Current | VDD = $V_{IN} = 3.465\text{V}$ | | | 100 | μA |
| | | VDD = $V_{IN} = 2.625\text{V}$ | | | 80 | |
| I_{IL} | Input Low Current | VDD = 3.465V, $V_{IN} = 0\text{V}$ | -5 | | | μA |
| | | VDD = 2.625V, $V_{IN} = 0\text{V}$ | -5 | | | |
| V_{OH} | Output High Voltage | VDDO = 3.3V $I_{OH} = -100\mu\text{A}$ | 2.9 | | | V |
| | | VDDO = 2.5V $I_{OH} = -100\mu\text{A}$ | 2.2 | | | V |
| V_{OL} | Output Low Voltage | VDDO = 3.3V $I_{OL} = 100\mu\text{A}$ | | | 0.2 | V |
| | | VDDO = 2.5V $I_{OL} = 100\mu\text{A}$ | | | 0.2 | V |

AC Characteristics, VDD = 3.3V ± 5%, T_A = -40°C to 85°C

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|---------------------|---|-----------------------------|------|------|------|-------|
| f _{MAX} | Output Frequency | VDDO = 3.3V | 4 | | 250 | MHz |
| | | VDDO = 2.5V | 4 | | 250 | |
| t _{pLH} | Propagation Delay, Low-to-High ⁽¹⁾ | VDDO = 3.3V, f ≤ 250MHz | 1.4 | | 2.2 | ns |
| | | VDDO = 2.5V, f ≤ 250MHz | 1.5 | | 3.0 | |
| t _{sk(o)} | Output Skew ⁽²⁾ | | | 25 | 80 | ps |
| t _{sk(pp)} | Part-to-Part Skew ⁽³⁾ | | | 250 | 800 | ps |
| t _R | Output Rise Time ⁽⁴⁾ | VDDO = 3.3V | 100 | 300 | 400 | ps |
| | | VDDO = 2.5V | 100 | 350 | 500 | |
| t _F | Output Fall Time ⁽⁴⁾ | VDDO = 3.3V | 100 | 300 | 400 | ps |
| | | VDDO = 2.5V | 100 | 350 | 500 | |
| odc | Output Duty Cycle ⁽⁵⁾ | f ≤ 133MHz | 48 | | 52 | % |
| | | 133MHz < f ≤ 200MHz | 47 | | 53 | % |
| | | 200MHz < f ≤ 250MHz | 47 | | 53 | % |
| t _{jit} | Additive RMS Jitter | 156.25MHz (@12kHz to 20MHz) | | 0.1 | | ps |
| | | 125MHz (@12kHz to 20MHz) | | 0.07 | | ps |

Note:

Parameters measured at f_{MAX} unless otherwise noted.

1. Measured from VDD /2 of the input to VDDO /2 of the output.
2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at VDDO /2.
3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at VDDO /2.
4. Defined from 20% to 80%
5. Measured at VDDO /2

AC Characteristics, $VDD = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $105^{\circ}C$

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|-----------|---|------------------------------|------|------|------|-------|
| f_{MAX} | Output Frequency | VDDO = 3.3V | 4 | | 250 | MHz |
| | | VDDO = 2.5V | 4 | | 250 | |
| t_{pLH} | Propagation Delay, Low-to-High ⁽¹⁾ | VDDO = 3.3V, $f \leq 250MHz$ | 1.4 | | 2.2 | ns |
| | | VDDO = 2.5V, $f \leq 250MHz$ | 1.5 | | 3.0 | |
| $tsk(o)$ | Output Skew ⁽²⁾ | | | 25 | 80 | ps |
| $tsk(pp)$ | Part-to-Part Skew ⁽³⁾ | | | 250 | 800 | ps |
| t_R | Output Rise Time ⁽⁴⁾ | VDDO = 3.3V | 100 | 300 | 400 | ps |
| | | VDDO = 2.5V | 100 | 350 | 500 | |
| t_F | Output Fall Time ⁽⁴⁾ | VDDO = 3.3V | 100 | 300 | 400 | ps |
| | | VDDO = 2.5V | 100 | 350 | 500 | |
| odc | Output Duty Cycle ⁽⁵⁾ | $f \leq 133MHz$ | 48 | | 52 | % |
| | | $133MHz < f \leq 200MHz$ | 47 | | 53 | % |
| | | $200MHz < f \leq 250MHz$ | 47 | | 53 | % |
| t_{jit} | Additive RMS Jitter | 156.25MHz (@12kHz to 20MHz) | | 0.1 | | ps |
| | | 125MHz (@12kHz to 20MHz) | | 0.07 | | ps |

Note:

 Parameters measured at f_{MAX} unless otherwise noted.

1. Measured from $VDD / 2$ of the input to $VDDO / 2$ of the output.
2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $VDDO / 2$.
3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $VDDO / 2$.
4. Defined from 20% to 80%
5. Measured at $VDDO / 2$

AC Characteristics, $V_{DD} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

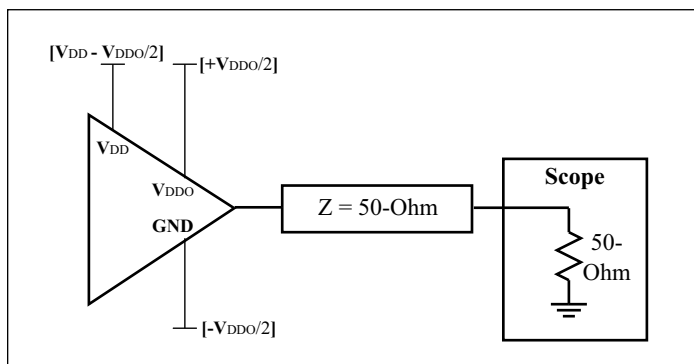
| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|-----------|---|---------------------------------|------|------|------|-------|
| f_{MAX} | Output Frequency | $V_{DDO} = 2.5V$ | 4 | | 250 | MHz |
| t_{pLH} | Propagation Delay, Low-to-High ⁽¹⁾ | $V_{DDO} = 2.5V, f \leq 250MHz$ | 1.5 | | 2.8 | ns |
| $tsk(o)$ | Output Skew ⁽²⁾ | | | 25 | 75 | ps |
| $tsk(pp)$ | Part-to-Part Skew ⁽³⁾ | | | 250 | 800 | ps |
| t_R | Output Rise Time ⁽⁴⁾ | $V_{DDO} = 2.5V$ | 100 | 350 | 500 | ps |
| t_F | Output Fall Time ⁽⁴⁾ | $V_{DDO} = 2.5V$ | 100 | 350 | 500 | ps |
| odc | Output Duty Cycle ⁽⁵⁾ | $f \leq 133MHz$ | 48 | | 52 | % |
| | | $133MHz < f \leq 200MHz$ | 47 | | 53 | % |
| | | $200MHz < f \leq 250MHz$ | 42 | | 58 | % |
| t_{jit} | Additive RMS Jitter | 156.25MHz (@12kHz to 20MHz) | | 0.1 | | ps |
| | | 125MHz (@12kHz to 20MHz) | | 0.07 | | ps |

Note:

Parameters measured at f_{MAX} unless otherwise noted.

1. Measured from $V_{DD} / 2$ of the input to $V_{DDO} / 2$ of the output.
2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO} / 2$.
3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $V_{DDO} / 2$.
4. Defined from 20% to 80%
5. Measured at $V_{DDO} / 2$

AC Test Circuit Load

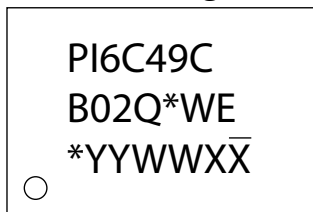


AC Characteristics, VDD = 2.5V ± 5%, T_A = -40°C to 105°C

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Units |
|------------------|---|-----------------------------|------|------|------|-------|
| f _{MAX} | Output Frequency | VDDO = 2.5V | 4 | | 250 | MHz |
| tp _{LH} | Propagation Delay, Low-to-High ⁽¹⁾ | VDDO = 2.5V, f ≤ 250MHz | 1.5 | | 2.8 | ns |
| tsk(o) | Output Skew ⁽²⁾ | | | 25 | 75 | ps |
| tsk(pp) | Part-to-Part Skew ⁽³⁾ | | | 250 | 800 | ps |
| t _R | Output Rise Time ⁽⁴⁾ | VDDO = 2.5V | 100 | 350 | 500 | ps |
| t _F | Output Fall Time ⁽⁴⁾ | VDDO = 2.5V | 100 | 350 | 500 | ps |
| odc | Output Duty Cycle ⁽⁵⁾ | f ≤ 133MHz | 48 | | 52 | % |
| | | 133MHz < f ≤ 200MHz | 47 | | 53 | % |
| | | 200MHz < f ≤ 250MHz | 42 | | 58 | % |
| t _{jit} | Additive RMS Jitter | 156.25MHz (@12kHz to 20MHz) | | 0.1 | | ps |
| | | 125MHz (@12kHz to 20MHz) | | 0.07 | | ps |

- Note:**
Parameters measured at f_{MAX} unless otherwise noted.
1. Measured from VDD /2 of the input to VDDO /2 of the output.
 2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at VDDO /2.
 3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at VDDO /2.
 4. Defined from 20% to 80%
 5. Measured at VDDO /2

Part Marking



- *: Die Rev (2 or 3)
- YY: Year
- WW: Workweek
- 1st X: Assembly Site Code
- 2nd X: Wafer Site Code

PI6C49CB02Q

Packaging Mechanical: 8-SOIC (W)

| SYMBOLS | MIN. | NOM. | MAX. |
|----------------|----------|------|------|
| A | — | — | 1.75 |
| A1 | 0.10 | — | 0.25 |
| A2 | 1.25 | — | — |
| b | 0.31 | — | 0.51 |
| c | 0.10 | — | 0.25 |
| D | 4.80 | 4.90 | 5.00 |
| E | 5.80 | 6.00 | 6.20 |
| E1 | 3.80 | 3.90 | 4.00 |
| e | 1.27 BSC | | |
| L | 0.40 | — | 1.27 |
| h | 0.25 | — | 0.50 |
| θ° | 0 | — | 8 |

UNIT : mm

NOTE :
 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES
 2. DIMENSIONS EXCLUDE BURRS, MOLD FLASH OR PROTRUSIONS
 3. REFER JEDEC MS-012

PERICOM
Enabling Serial Connectivity

DATE: 02/21/14

DESCRIPTION: 8-Pin, 150mil-Wide, SOIC

PACKAGE CODE: W (W8)

DOCUMENT CONTROL #: PD-1001

REVISION: G

15-0103

For latest package info.

please check: <http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/>

Ordering Information

| Ordering Code | Package Code | Operating Temperature | Package Description |
|-----------------|--------------|-----------------------|---------------------------|
| PI6C49CB02Q2WEX | W | -40 to 105°C | 8-pin, 150mil-Wide (SOIC) |
| PI6C49CB02Q3WEX | W | -40 to 85°C | 8-pin, 150mil-Wide (SOIC) |

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Q = Automotive Compliant
5. 2 and 3 = AEC-Q100 Grade Level
6. E = Pb-free and Green
7. X suffix = Tape/Reel

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[ADCLK905BCPZ-R7](#) [ADCLK907BCPZ-R2](#) [ADCLK907BCPZ-WP](#) [ADCLK914BCPZ-R2](#) [ADCLK914BCPZ-R7](#) [ADCLK925BCPZ-R2](#)
[ADCLK925BCPZ-R7](#)